

## SKiiP 3-phase bridge

Absolute Maximum Ratings			
Symbol	Conditions <sup>1)</sup>	Values	Units
V <sub>isol</sub> <sup>4)</sup>	AC, 1min	3000	V
T <sub>op</sub> , T <sub>stg</sub>	Operating / stor. temperature	-25...+85	°C
IGBT and Inverse Diode			
V <sub>CES</sub> <sup>5)</sup>		1200	V
V <sub>CC</sub>	Operating DC link voltage	900	V
I <sub>C</sub>	IGBT	200	A
T <sub>j</sub> <sup>3)</sup>	IGBT + Diode	-40...+150	°C
I <sub>F</sub>	Diode	200	A
I <sub>FM</sub>	Diode, t <sub>p</sub> < 1 ms	400	A
I <sub>FSM</sub>	Diode, T <sub>j</sub> = 150 °C, 10ms; sin	1440	A
I <sup>2</sup> t (Diode)	Diode, T <sub>j</sub> = 150 °C, 10ms	10	kAs <sup>2</sup>
Driver			
V <sub>S1</sub>	Stabilized Power Supply	18	V
V <sub>S2</sub>	Non-stabilized Power Supply	30	V
f <sub>smax</sub>	Switching frequency	20	kHz
dV/dt	Primary to secondary side	75	kV/μs

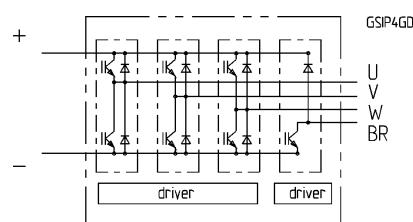
Characteristics					
Symbol	Conditions <sup>1)</sup>	min.	typ.	max.	Units
IGBT <sup>11)</sup>					
V <sub>(BR)CES</sub>	Driver without supply	≥V <sub>CES</sub>	—	—	V
I <sub>CES</sub>	V <sub>GE</sub> = 0, T <sub>j</sub> = 25 °C	—	—	0,4	mA
	V <sub>CE</sub> = V <sub>CES</sub> T <sub>j</sub> = 125 °C	—	10	—	mA
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	—	—	1,38	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	—	—	10,5	mΩ
V <sub>Cesat</sub>	I <sub>C</sub> = 175A, T <sub>j</sub> = 125 °C	—	—	3,2	V
V <sub>Cesat</sub>	I <sub>C</sub> = 175A, T <sub>j</sub> = 25 °C	—	—	3,05	V
E <sub>on</sub> + E <sub>off</sub>	V <sub>CC</sub> =600/900V, I <sub>C</sub> =200A T <sub>j</sub> = 125 °C	—	—	60/98	mJ
C <sub>CHC</sub>	per SKiiP, AC side	—	1,4	—	nF
L <sub>CE</sub>	Top, Bottom	—	15	—	nH
Inverse Diode <sup>2)</sup>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 175A; T <sub>j</sub> = 125 °C	—	—	2,45	V
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 175A; T <sub>j</sub> = 25 °C	—	—	2,55	V
E <sub>on</sub> + E <sub>off</sub>	I <sub>F</sub> = 200A; T <sub>j</sub> = 125 °C	—	—	8	mJ
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	—	0,91	—	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	—	5,7	—	mΩ
Thermal Characteristics					
R <sub>thjs</sub> <sup>10)</sup>	per IGBT	—	—	0,129	°C/W
R <sub>thjs</sub> <sup>10)</sup>	per Diode	—	—	0,375	°C/W
R <sub>thsa</sub> <sup>6,10)</sup>	P16 heatsink; see case	—	—	0,033	°C/W
Driver					
I <sub>S1</sub>	Supply current 15V-supply	340+360*f <sub>s</sub> /f <sub>smax</sub> +3,5*I <sub>AC</sub> /A		mA	
I <sub>S2</sub>	Supply current 24V-supply	250+240*f <sub>s</sub> /f <sub>smax</sub> +2,6*I <sub>AC</sub> /A		mA	
t <sub>interlock-driver</sub>	Interlock-time	2,3		μs	
SKiiPPACK protection					
I <sub>TRIPSC</sub>	Short circuit protection	250 ± 2%		A	
I <sub>TRIPLG</sub>	Ground fault protection	58 +/- 2%		A	
T <sub>TRIP</sub>	Over-temp. protection	115 ± 5%		°C	
U <sub>DCTRIP</sub> <sup>9)</sup>	U <sub>DC</sub> -protection	920 ± 2%		V	
Mechanical Data					
M1	DC terminals, SI Units	4	—	6	Nm
M2	AC terminals, SI Units	8	—	10	Nm

## SKiiPPACK®

SK integrated intelligent Power PACK  
3-phase bridge with brake chopper (E/A)  
SKiiP

### 232 GDL 120 - 410 CTV <sup>7,9)</sup>

Preliminary Data  
Case S5GDL



## Features

- Short circuit protection, due to evaluation of current sensor signals
- Isolated power supply
- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Over-temperature protection

<sup>1)</sup> T<sub>heatsink</sub> = 25 °C, unless otherwise specified

<sup>2)</sup> CAL = Controlled Axial Lifetime Technology (soft and fast)

<sup>3)</sup> without driver

<sup>4)</sup> Driver input to DC link/ AC output to heatsink

<sup>5)</sup> with Semikron-DC link (low inductance)

<sup>6)</sup> other heatsinks on request

<sup>7)</sup> C - Integrated current sensors

T - Temperature protection

V - 15 V or 24 V power supply options available for driver:

U - DC link voltage sense

F - Fiber optic connector

<sup>8)</sup> "s" referenced to temperature sensor

<sup>10)</sup> NPT-technology with homogenous current-distribution

## SKiiP Brake-chopper

Symbol	Conditions <sup>1)</sup>	Values	Units
V <sub>isol</sub> <sup>4)</sup>	AC, 1min	3000	V
T <sub>op</sub> , T <sub>stg</sub>	Operating / stor. temperature	-25...+85	°C
IGBT and Inverse Diode			
V <sub>CES</sub> <sup>5)</sup>		1200	V
V <sub>CC</sub>	Operating DC link voltage	900	V
I <sub>C</sub>	IGBT	200	A
T <sub>j</sub> <sup>3)</sup>	IGBT + Diode	-40...+150	°C
I <sub>F</sub>	Diode	200	A
I <sub>FM</sub>	Diode, t <sub>p</sub> < 1 ms	400	A
I <sub>FSM</sub>	Diode, T <sub>j</sub> = 150 °C, 10ms; sin	1440	A
I <sup>2</sup> t (Diode)	Diode, T <sub>j</sub> = 150 °C, 10ms	10	kAs <sup>2</sup>
Driver			
V <sub>S1</sub>	Stabilized Power Supply	18	V
V <sub>S2</sub>	Non-stabilized Power Supply	30	V
f <sub>smax</sub>	Switching frequency	5	kHz
dV/dt	Primary to secondary side	50	kV/μs

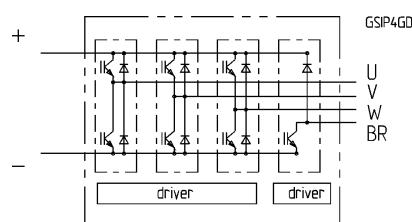
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IGBT <sup>11)</sup>					
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I <sub>CES</sub>	V <sub>GE</sub> = 0, T <sub>j</sub> = 25 °C V <sub>CE</sub> = V <sub>CES</sub> T <sub>j</sub> = 125 °C	—	—	0,4	mA
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	—	—	1,38	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	—	—	10,5	mΩ
V <sub>Cesat</sub>	I <sub>C</sub> = 175A, T <sub>j</sub> = 125 °C	—	—	3,2	V
V <sub>Cesat</sub>	I <sub>C</sub> = 175A, T <sub>j</sub> = 25 °C	—	—	3,05	V
E <sub>on</sub> + E <sub>off</sub>	V <sub>CC</sub> =600/900V, I <sub>C</sub> =200A T <sub>j</sub> = 125 °C	—	—	60/98	mJ
C <sub>CHC</sub>	per SKiiP, AC side	—	1,4	—	nF
L <sub>CE</sub>	Top, Bottom	—	15	—	nH
Inverse Diode <sup>2)</sup>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 175A; T <sub>j</sub> = 125 °C	—	—	2,45	V
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E <sub>on</sub> + E <sub>off</sub>	I <sub>F</sub> = 200A; T <sub>j</sub> = 125 °C	—	—	8	mJ
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	—	0,91	—	V
r <sub>T</sub>	T <sub>j</sub> = 125 °C	—	5,7	—	mΩ
Thermal Characteristics					
R <sub>thjs</sub> <sup>10)</sup>	per IGBT	—	—	0,129	°C/W
R <sub>thjs</sub> <sup>10)</sup>	per Diode	—	—	0,375	°C/W
R <sub>thsa</sub> <sup>6,10)</sup>	P16 heatsink; see case	—	—	0,033	°C/W
Driver					
I <sub>S1</sub>	Supply current 15V-supply	67+10*f <sub>s</sub> /f <sub>smax</sub> +0*I <sub>AC</sub> /A		mA	
I <sub>S2</sub>	Supply current 24V-supply	67+10*f <sub>s</sub> /f <sub>smax</sub> +0,0*I <sub>AC</sub> /A		mA	
t <sub>interlock-driver</sub>	Interlock-time	2,3			μs
SKiiPPACK protection					
I <sub>TRIPSC</sub>	Short circuit protection	250 ± 2%		A	
I <sub>TRIPLG</sub>	Ground fault protection	-		A	
T <sub>TRIP</sub>	Over-temp. protection	115 ± 5%		°C	
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<sup>6)</sup> other heatsinks on request

<sup>7)</sup> C - Integrated current sensors

T - Temperature protection

V - 15 V or 24 V power supply

E - adapted to 400 Vrms; U - adapted to 460 Vrms

<sup>9)</sup> options available for driver:  
U - DC link voltage sense

F - Fiber optic connector

<sup>10)</sup> "s" referenced to temperature sensor

<sup>11)</sup> NPT-technology with homogenous current-distribution